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8-Mbit (512K words × 16-bit) Static RAM with Error-Correcting Code (ECC)

Features

- AEC-Q100 Qualified
- Ultra-low standby power
 - Typical standby current: 5 μ A
 - Maximum standby current: 35 μ A
- High speed: 45 ns/55 ns
- Embedded error-correcting code (ECC) for single-bit error correction^[1, 2]
- Temperature ranges:
 - Automotive-A: -40 °C to +85 °C
- Wide operating voltage range: 1.65 V to 2.2 V, 2.2 V to 3.6 V
- 1.5-V data retention
- Transistor-transistor logic (TTL)-compatible inputs and outputs
- Available in Pb-free 48-ball VFBGA, 48-pin TSOP II, and 44-pin TSOP I packages

Functional Description

CY62157G is a high-performance CMOS low-power (MoBL[®]) SRAM device with embedded ECC. This device is offered in dual chip-enable.

Devices with dual chip-enable are accessed by asserting both chip-enable inputs – \overline{CE}_1 as LOW and CE_2 as HIGH.

Data writes are performed by asserting the Write Enable input (\overline{WE}) LOW, and providing the data and address on device data (I/O_0 through I/O_{15}) and address (A_0 through A_{19}) pins respectively. The Byte High/Low Enable (\overline{BHE} , \overline{BLE}) inputs control byte writes, and write data on the corresponding I/O lines to the memory location specified. \overline{BHE} controls I/O_8 through I/O_{15} ; \overline{BLE} controls I/O_0 through I/O_7 .

Data reads are performed by asserting the Output Enable (\overline{OE}) input and providing the required address on the address lines. Read data is accessible on I/O lines (I/O_0 through I/O_{15}). Byte accesses can be performed by asserting the required byte enable signal (\overline{BHE} , \overline{BLE}) to read either the upper byte or the lower byte of data from the specified address location.

All I/O s (I/O_0 through I/O_{15}) are placed in a HI-Z state when the device is deselected (\overline{CE}_1 HIGH / CE_2 LOW for dual chip-enable device), or control signals are de-asserted (\overline{OE} , \overline{BLE} , and \overline{BHE}).

These devices also have a unique “Byte Power down” feature where if both the Byte Enables (\overline{BHE} and \overline{BLE}) are disabled, the device seamlessly switches to standby mode irrespective of the state of the chip enable(s), thereby saving power.

The CY62157G device is available in a Pb-free 48-ball VFBGA, 48-pin TSOP I, and 44-pin TSOP II packages. Refer to the [Logic Block Diagram – CY62157G on page 2](#), the [Pin Configurations on page 4](#), and the associated footnotes for details.

Product Portfolio

Product	Range	V _{CC} Range (V)	Speed (ns)	Power Dissipation			
				Operating I _{CC} , (mA), f = f _{max}		Standby, I _{SB2} (μ A)	
				Typ ^[3]	Max	Typ ^[3]	Max
CY62157G18	Automotive-A	1.65 V to 2.2 V	55	18	22	4.5	8
CY62157G30		2.2 V to 3.6 V	45	18	25	1.4	6.5

Notes

1. SER FIT rate <0.1 FIT/Mb. Refer to [AN88889](#) for details.
2. This device does not support automatic write-back on error detection.
3. Indicates the value for the center of distribution at 3.0 V (or 1.8 V), 25 °C and not 100% tested.

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Pin Configurations

Figure 1. 48-ball VFBGA Pinout [4]

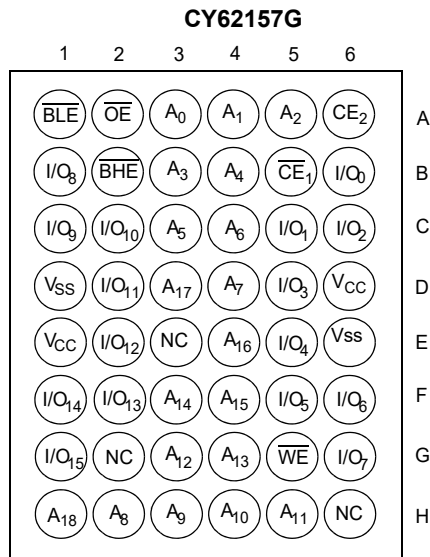
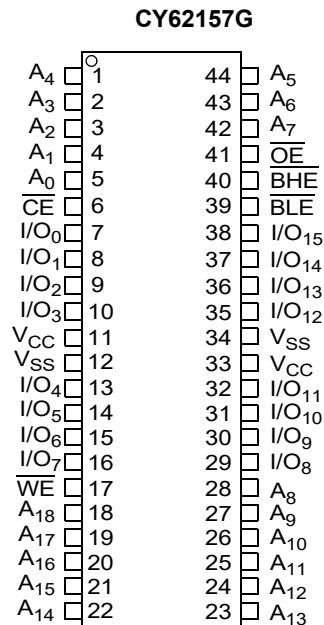


Figure 2. 44-pin TSOP II Pinout [4]

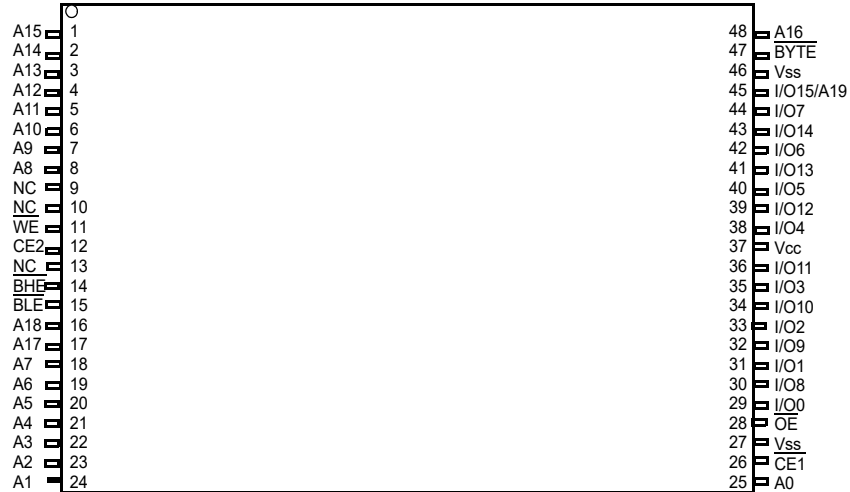


Note

- NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.

Pin Configurations

Figure 3. 48-pin TSOP I Pinout (Top View) [5, 6]



Notes

- NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.
- Tie the $\overline{\text{BYTE}}$ pin in the 48-pin TSOP I package to V_{CC} to use the device as a 512K × 16 SRAM. The 48-pin TSOP I package can also be used as a 1M × 8 SRAM by tying the $\overline{\text{BYTE}}$ signal to V_{SS} . In the 1M × 8 configuration, Pin 45 is the extra address line A19, while $\overline{\text{BHE}}$, $\overline{\text{BLE}}$, and I/O₈ to I/O₁₄ pins are not used and can be left floating.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature -65 °C to + 150 °C
 Ambient temperature
 with power applied -55 °C to + 125 °C
 Supply voltage
 to ground potential ^[7] -0.5 V to V_{CC} + 0.5 V
 DC voltage applied to outputs
 in HI-Z state ^[7] -0.5 V to V_{CC} + 0.5 V

DC input voltage ^[7] -0.5 V to V_{CC} + 0.5 V
 Output current into outputs (LOW) 20 mA
 Static discharge voltage
 (MIL-STD-883, Method 3015) >2001 V
 Latch-up current >140 mA

Operating Range

Grade	Ambient Temperature	V _{CC}
Automotive-A	-40 °C to +85 °C	1.65 V to 2.2 V 2.2 V to 3.6 V

Note

7. V_{IL(min)} = -2.0 V and V_{IH(max)} = V_{CC} + 2 V for pulse durations of <2 ns.

DC Electrical Characteristics

Over the Operating Range

Parameter	Description		Test Conditions	45/55 ns (Automotive-A)			Unit	
				Min	Typ ^[9]	Max		
V _{OH}	Output HIGH voltage	1.65 V to 2.2 V	V _{CC} = Min, I _{OH} = -0.1 mA	1.4	-	-	V	
		2.2 V to 2.7 V	V _{CC} = Min, I _{OH} = -0.1 mA	2.0	-	-		
		2.7 V to 3.6 V	V _{CC} = Min, I _{OH} = -1.0 mA	2.4	-	-		
V _{OL}	Output LOW voltage	1.65 V to 2.2 V	V _{CC} = Min, I _{OL} = 0.1 mA	-	-	0.2	V	
		2.2 V to 2.7 V	V _{CC} = Min, I _{OL} = 0.1 mA	-	-	0.4		
		2.7 V to 3.6 V	V _{CC} = Min, I _{OL} = 2.1 mA	-	-	0.4		
V _{IH}	Input HIGH voltage ^[8]	1.65 V to 2.2 V	-	1.4	-	V _{CC} + 0.2	V	
		2.2 V to 2.7 V	-	1.8	-	V _{CC} + 0.3		
		2.7 V to 3.6 V	-	2.0	-	V _{CC} + 0.3		
V _{IL}	Input LOW voltage ^[8]	1.65 V to 2.2 V	-	-0.2	-	0.4	V	
		2.2 V to 2.7 V	-	-0.3	-	0.6		
		2.7 V to 3.6 V	-	-0.3	-	0.8		
I _{IX}	Input leakage current		GND ≤ V _{IN} ≤ V _{CC}	-1.0	-	+1.0	μA	
I _{OZ}	Output leakage current		GND ≤ V _{OUT} ≤ V _{CC} , Output disabled	-1.0	-	+1.0	μA	
I _{CC}	V _{CC} operating supply current	1.65 V to 2.2 V	V _{CC} = Max, I _{OUT} = 0 mA, CMOS levels	f = f _{MAX}	-	18	22	mA
				f = 1 MHz	-	6	7	mA
		2.2 V to 3.6 V	V _{CC} = Max, I _{OUT} = 0 mA, CMOS levels	f = f _{MAX}	-	18	25	mA
				f = 1 MHz	-	6	7	mA
I _{SB1} ^[10]	Automatic power down current – CMOS inputs; V _{CC} = 2.2 to 3.6 V	$\overline{CE}_1 \geq V_{CC} - 0.2 V$ or $CE_2 \leq 0.2 V$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 V$,		-	1.4	6.5	μA	
I _{SB1} ^[10]	Automatic power down current – CMOS inputs; V _{CC} = 1.65 to 2.2 V	$V_{IN} \geq V_{CC} - 0.2 V$ or $V_{IN} \leq 0.2 V$, $f = f_{max}$ (address and data only), $f = 0$ (OE, and WE), $V_{CC} = V_{CC(max)}$		-	-	8	μA	
I _{SB2} ^[10]	Automatic power down current – CMOS inputs; V _{CC} = 2.2 to 3.6 V	$\overline{CE}_1 \geq V_{CC} - 0.2 V$ or $CE_2 \leq 0.2 V$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 V$,		-	1.4	6.5 ^[11]	μA	
I _{SB2} ^[10]	Automatic power down current – CMOS inputs; V _{CC} = 1.65 to 2.2 V	$V_{IN} \geq V_{CC} - 0.2 V$ or $V_{IN} \leq 0.2 V$, $f = 0$, V _{CC} = V _{CC(max)}		-	-	8	μA	

Notes

8. V_{IL(min)} = -2.0 V and V_{IH(max)} = V_{CC} + 2 V for pulse durations of < 2 ns.

9. Indicates the value for the center of Distribution at 3.0 V (or 1.8V), 25 °C and not 100% tested.

10. Chip enables (\overline{CE}_1 and CE₂) and \overline{BHE} , \overline{BLE} must be tied to CMOS levels to meet the I_{SB1}/I_{SB2}/I_{CCDR} spec. Other inputs can be left floating.

11. I_{SB2} (max.) for 44TSOP package = 8uA, only when the chip is deselected by disabling both BHE and BLE.

Capacitance

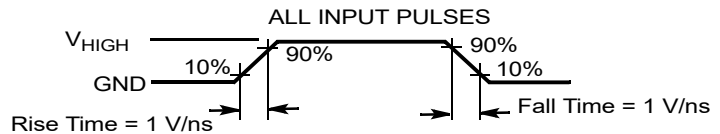
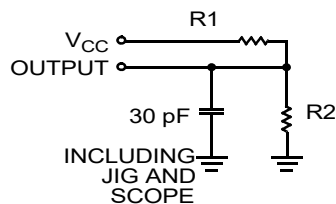
Parameter ^[12]	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = V _{CC(typ)}	10	pF
C _{OUT}	Output capacitance		10	pF

Thermal Resistance

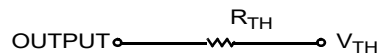
Parameter ^[12]	Description	Test Conditions	48-ball VFBGA	44-pin TSOP II	48-pin TSOP I	Unit
Θ _{JA}	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	36.92	65.91	60.07	°C/W
Θ _{JC}	Thermal resistance (junction to case)		13.55	13.96	9.73	°C/W

AC Test Loads and Waveforms

Figure 4. AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT



Parameters	1.8 V	2.5 V	3.0 V	Unit
R1	13500	16667	1103	Ω
R2	10800	15385	1554	Ω
R _{TH}	6000	8000	645	Ω
V _{TH}	0.80	1.20	1.75	V

Note

12. Tested initially and after any design or process changes that may affect these parameters.

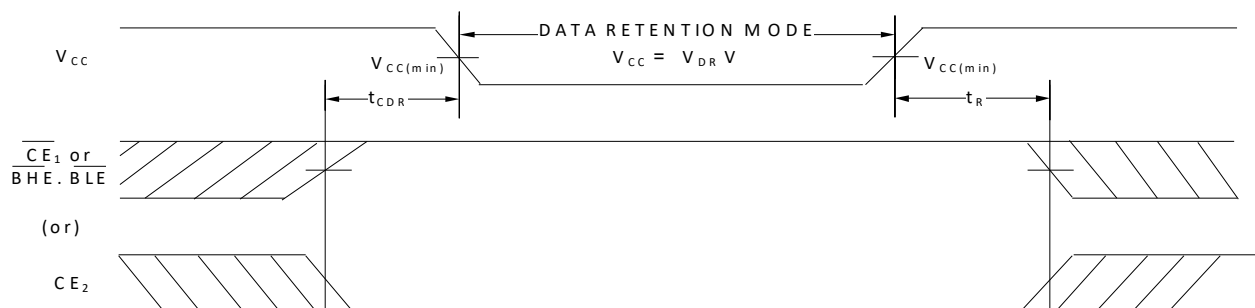
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	(Automotive-A)			Unit	
			Min	Typ ^[13]	Max		
V _{DR}	V _{CC} for data retention	2.2 V < V _{CC} ≤ 3.6 V	1	–	–	V	
		1.65 V < V _{CC} ≤ 2.2 V	1	–	–	V	
I _{CCDR} ^[14]	Data-retention current (For 3.3-V typical device)	$\overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}$ or $CE_2 \leq 0.2 \text{ V}$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 \text{ V}$, $V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$	2.2 V < V _{CC} ≤ 3.6 V	–	1.4	6.5	μA
		$\overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}$ or $CE_2 \leq 0.2 \text{ V}$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 \text{ V}$, $V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$	V _{CC} = 1.5 V	–	3.2	8	μA
		$\overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}$ or $CE_2 \leq 0.2 \text{ V}$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 \text{ V}$, $V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$	V _{CC} = 1.2 V	–	4	9	μA
		$\overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}$ or $CE_2 \leq 0.2 \text{ V}$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 \text{ V}$, $V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$					
	Data-retention current (For 1.8V Typical device)	$1.2 \text{ V} < V_{CC} \leq 2.2 \text{ V}$ $\overline{CE}_1 \geq V_{CC} - 0.2 \text{ V}$ or $CE_2 \leq 0.2 \text{ V}$ or $(\overline{BHE} \text{ and } \overline{BLE}) \geq V_{CC} - 0.2 \text{ V}$, $V_{IN} \geq V_{CC} - 0.2 \text{ V}$ or $V_{IN} \leq 0.2 \text{ V}$		–	5	9	–
t _{CDR} ^[15]	Chip deselect to data-retention time	–	0	–	–	–	
t _R ^[16]	Operation-recovery time	–	45/55	–	–	ns	

Data Retention Waveform

Figure 5. Data-Retention Waveform ^[17]



Notes

13. Indicates the value for the center of distribution at 3.0 V, 25°C and not 100% tested.
14. Chip enables (\overline{CE}_1 and CE_2) must be tied to CMOS levels to meet the $I_{SB1}/I_{SB2}/I_{CCDR}$ spec. Other inputs can be left floating.
15. Tested initially and after any design or process changes that may affect these parameters.
16. Full device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} ≥ 100 μs or stable at V_{CC(min)} ≥ 100 μs.
17. $\overline{BHE}.\overline{BLE}$ is the AND of both \overline{BHE} and \overline{BLE} . Deselect the chip by either disabling the chip enable signals or by disabling both \overline{BHE} and \overline{BLE} .

Switching Characteristics

Parameter ^[18]	Description	55 ns		45 ns		Unit
		Min	Max	Min	Max	
Read Cycle						
t_{RC}	Read cycle time	55	–	45	–	ns
t_{AA}	Address to data valid	–	55	–	45	ns
t_{OHA}	Data hold from address change	10	–	10	–	ns
t_{ACE}	\overline{CE}_1 LOW and CE_2 HIGH to data valid / \overline{CE} LOW	–	55	–	45	ns
t_{DOE}	\overline{OE} LOW to data valid / \overline{OE} LOW	–	25	–	22	ns
t_{LZOE}	\overline{OE} LOW to Low Z ^[19]	5	–	5	–	ns
t_{HZOE}	\overline{OE} HIGH to High Z ^[19, 20]	–	20	–	18	ns
t_{LZCE}	\overline{CE}_1 LOW and CE_2 HIGH to Low Z ^[19]	10	–	10	–	ns
t_{HZCE}	\overline{CE}_1 HIGH and CE_2 LOW to High Z ^[19, 20]	–	20	–	18	ns
t_{PU}	\overline{CE}_1 LOW and CE_2 HIGH to power-up	0	–	0	–	ns
t_{PD}	\overline{CE}_1 HIGH and CE_2 LOW to power-down	–	55	–	45	ns
t_{DBE}	\overline{BLE} / \overline{BHE} LOW to data valid	–	55	–	45	ns
t_{LZBE}	\overline{BLE} / \overline{BHE} LOW to Low Z ^[19]	5	–	5	–	ns
t_{HZBE}	\overline{BLE} / \overline{BHE} HIGH to High Z ^[19, 20]	–	20	–	18	ns
Write Cycle ^[21,22]						
t_{WC}	Write cycle time	55	–	45	–	ns
t_{SCE}	\overline{CE}_1 LOW and CE_2 HIGH to write end	40	–	35	–	ns
t_{AW}	Address setup to write end	40	–	35	–	ns
t_{HA}	Address hold from write end	0	–	0	–	ns
t_{SA}	Address setup to write start	0	–	0	–	ns
t_{PWE}	\overline{WE} pulse width	40	–	35	–	ns
t_{BW}	\overline{BLE} / \overline{BHE} LOW to write end	40	–	35	–	ns
t_{SD}	Data setup to write end	25	–	25	–	ns
t_{HD}	Data hold from write end	0	–	0	–	ns
t_{HZWE}	\overline{WE} LOW to High Z ^[19, 20]	–	20	–	18	ns
t_{LZWE}	\overline{WE} HIGH to Low Z ^[19]	10	–	10	–	ns

Notes

18. Test conditions assume signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for $V_{CC} \geq 3$ V) and $V_{CC}/2$ (for $V_{CC} < 3$ V), and input pulse levels of 0 to 3 V (for $V_{CC} \geq 3$ V) and 0 to V_{CC} (for $V_{CC} < 3$ V). Test conditions for the read cycle use output loading shown in AC Test Loads and Waveforms section, unless specified otherwise.

19. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZBE} is less than t_{LZBE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any device.

20. t_{HZOE} , t_{HZCE} , t_{HZBE} , and t_{HZWE} transitions are measured when the outputs enter a high impedance state.

21. The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{IL}$, $\overline{CE}_1 = V_{IL}$, \overline{BHE} or \overline{BLE} or both = V_{IL} , and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write. Any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.

22. The minimum write cycle pulse width for the Write Cycle No. 3 (\overline{WE} Controlled, \overline{OE} LOW) should be equal to the sum of t_{SD} and t_{HZWE} .

Switching Waveforms

Figure 6. Read Cycle No. 1 of CY62157G (Address Transition Controlled) [23, 24]

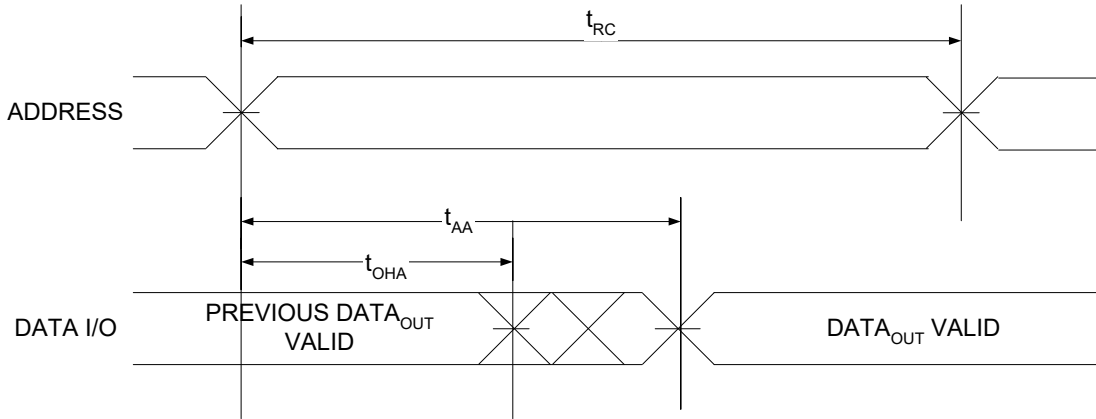
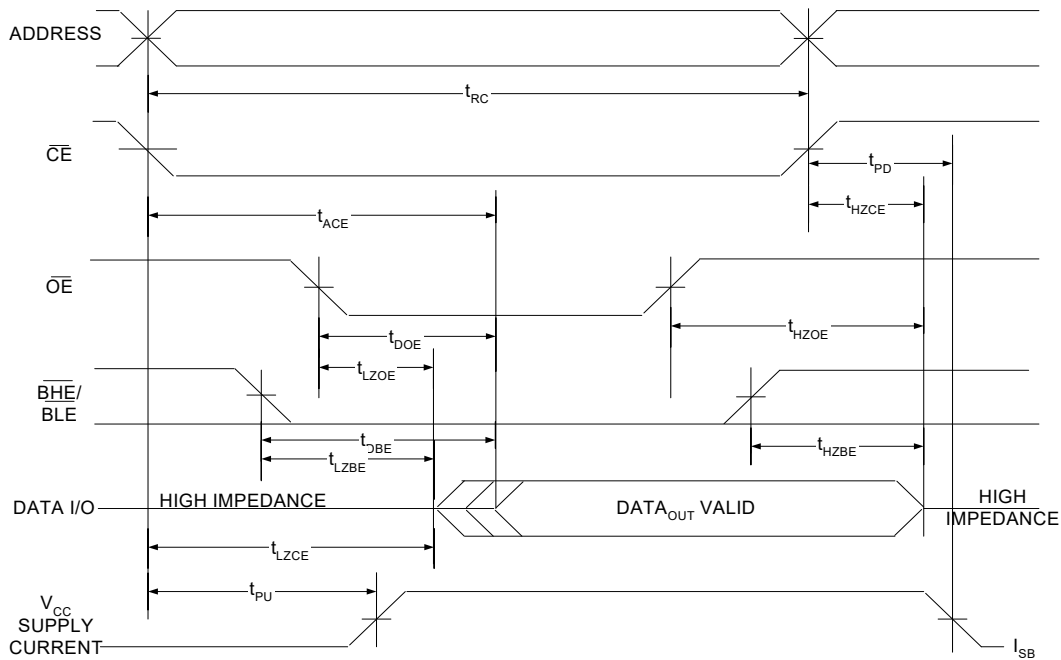


Figure 7. Read Cycle No. 2 (\overline{OE} Controlled) [24, 25, 26]



Notes

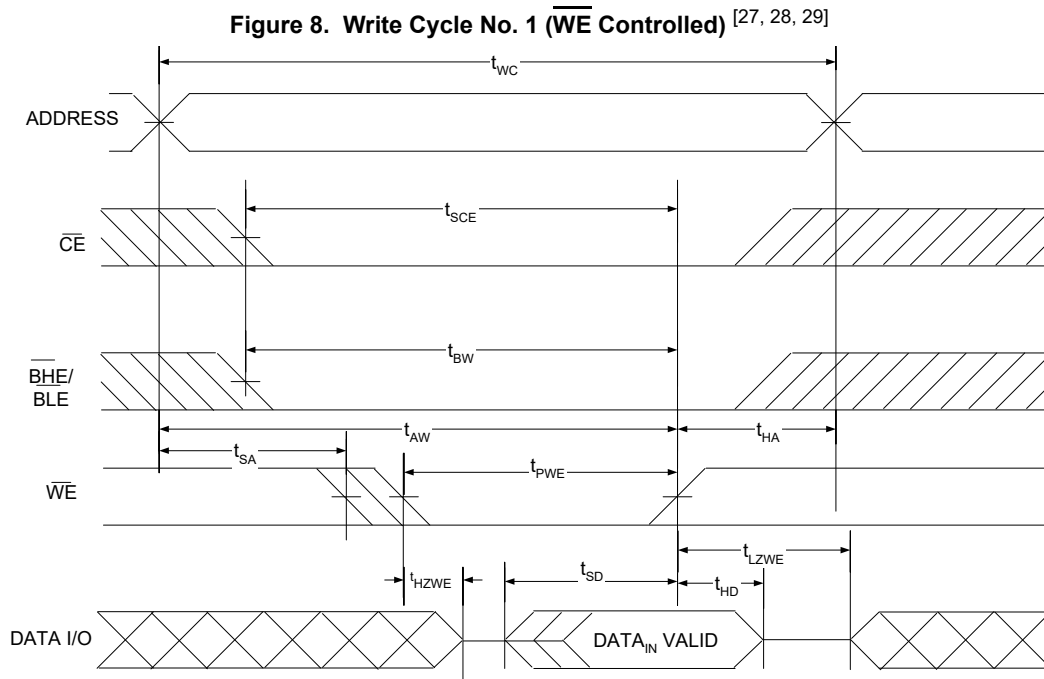
23. The device is continuously selected. $\overline{OE} = V_{IL}$, $\overline{CE} = V_{IL}$, \overline{BHE} or \overline{BLE} or both = V_{IL} .

24. \overline{WE} is HIGH for read cycle.

25. For all dual chip enable devices, \overline{CE} is the logical combination of \overline{CE}_1 and CE_2 . When \overline{CE}_1 is LOW and CE_2 is HIGH, \overline{CE} is LOW; when \overline{CE}_1 is HIGH or CE_2 is LOW, \overline{CE} is HIGH.

26. Address valid prior to or coincident with \overline{CE} LOW transition.

Switching Waveforms (continued)

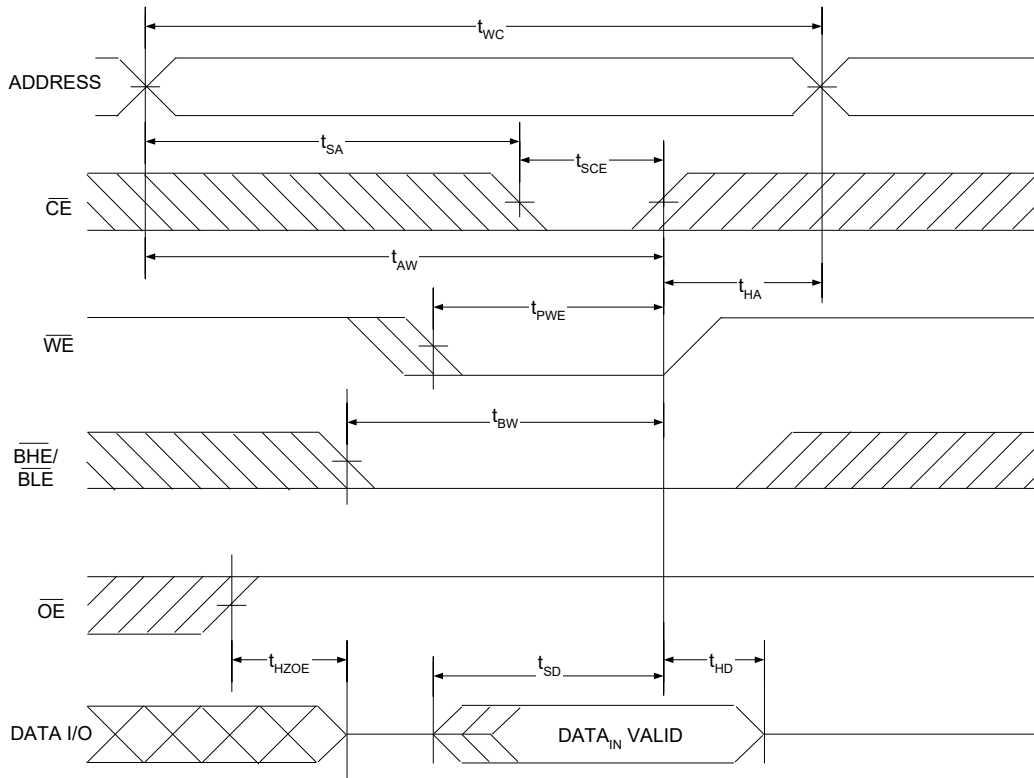


Notes

27. For all dual chip enable devices, $\overline{\text{CE}}$ is the logical combination of $\overline{\text{CE}}_1$ and CE_2 . When $\overline{\text{CE}}_1$ is LOW and CE_2 is HIGH, $\overline{\text{CE}}$ is LOW; when $\overline{\text{CE}}_1$ is HIGH or CE_2 is LOW, $\overline{\text{CE}}$ is HIGH.
28. The internal write time of the memory is defined by the overlap of $\overline{\text{WE}} = V_{\text{IL}}$, $\overline{\text{CE}}_1 = V_{\text{IL}}$, $\overline{\text{BHE}}$ or $\overline{\text{BLE}}$ or both = V_{IL} , and $\text{CE}_2 = V_{\text{IH}}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
29. Data I/O is in HI-Z state if $\overline{\text{CE}} = V_{\text{IH}}$, or $\overline{\text{OE}} = V_{\text{IH}}$ or $\overline{\text{BHE}}$, and/or $\overline{\text{BLE}} = V_{\text{IH}}$.

Switching Waveforms (continued)

Figure 9. Write Cycle No. 2 (\overline{CE} Controlled) [30, 31, 32]

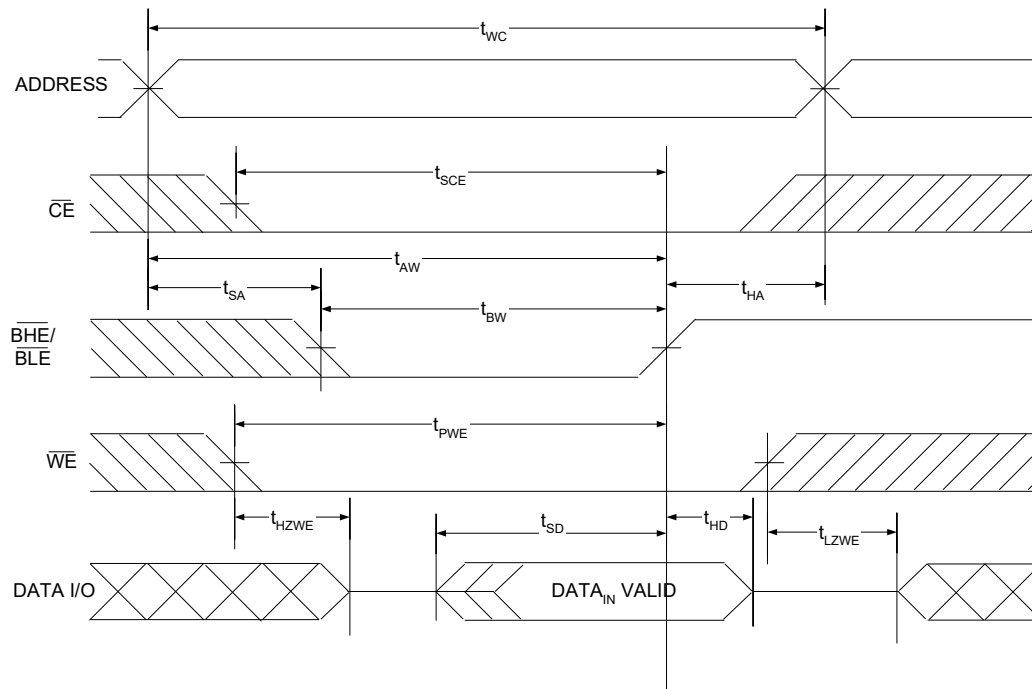


Notes

- 30. For all dual chip enable devices, \overline{CE} is the logical combination of \overline{CE}_1 and CE_2 . When \overline{CE}_1 is LOW and CE_2 is HIGH, \overline{CE} is LOW; when \overline{CE}_1 is HIGH or CE_2 is LOW, \overline{CE} is HIGH.
- 31. The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{IL}$, $\overline{CE}_1 = V_{IL}$, \overline{BHE} or \overline{BLE} or both = V_{IL} , and $CE_2 = V_{IH}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
- 32. Data I/O is in high impedance state if $\overline{CE} = V_{IH}$, or $\overline{OE} = V_{IH}$ or \overline{BHE} , and/or $\overline{BLE} = V_{IH}$.

Switching Waveforms (continued)

Figure 10. Write Cycle No. 3 ($\overline{\text{BHE}}/\overline{\text{BLE}}$ controlled, $\overline{\text{OE}}$ LOW) [33, 34, 35]



Notes

33. For all dual chip enable devices, $\overline{\text{CE}}$ is the logical combination of $\overline{\text{CE}}_1$ and CE_2 . When $\overline{\text{CE}}_1$ is LOW and CE_2 is HIGH, $\overline{\text{CE}}$ is LOW; when $\overline{\text{CE}}_1$ is HIGH or CE_2 is LOW, $\overline{\text{CE}}$ is HIGH.
34. The internal write time of the memory is defined by the overlap of $\overline{\text{WE}} = V_{\text{IL}}$, $\overline{\text{CE}}_1 = V_{\text{IL}}$, $\overline{\text{BHE}}$ or $\overline{\text{BLE}}$ or both = V_{IL} , and $\text{CE}_2 = V_{\text{IH}}$. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
35. Data I/O is in high impedance state if $\overline{\text{CE}} = V_{\text{IH}}$, or $\overline{\text{OE}} = V_{\text{IH}}$ or $\overline{\text{BHE}}$, and/or $\overline{\text{BLE}} = V_{\text{IH}}$.

Truth Table – CY62157G

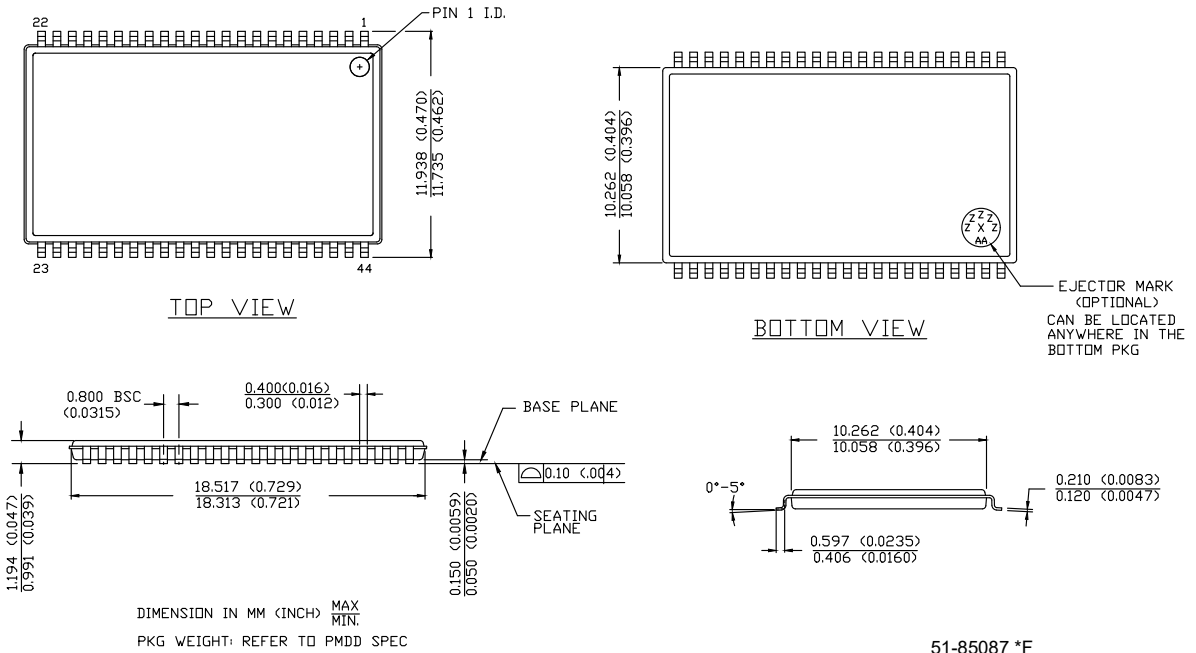
\overline{CE}_1	CE_2	\overline{WE}	\overline{OE}	\overline{BHE}	\overline{BLE}	Inputs/Outputs	Mode	Power
H	X ^[36]	X	X	X	X	HI-Z	Deselect/Power-down	Standby (I_{SB})
X ^[36]	L	X	X	X	X	HI-Z	Deselect/Power-down	Standby (I_{SB})
X ^[36]	X ^[36]	X	X	H	H	HI-Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0 – I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0 – I/O_7); HI-Z (I/O_8 – I/O_{15})	Read	Active (I_{CC})
L	H	H	L	L	H	HI-Z (I/O_0 – I/O_7); Data Out (I/O_8 – I/O_{15})	Read	Active (I_{CC})
L	H	H	H	X	X	HI-Z	Output disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0 – I/O_{15})	Write	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0 – I/O_7); HI-Z (I/O_8 – I/O_{15})	Write	Active (I_{CC})
L	H	L	X	L	H	HI-Z (I/O_0 – I/O_7); Data In (I/O_8 – I/O_{15})	Write	Active (I_{CC})

Note

36. The 'X' (Don't care) state for the chip enables refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

Package Diagrams

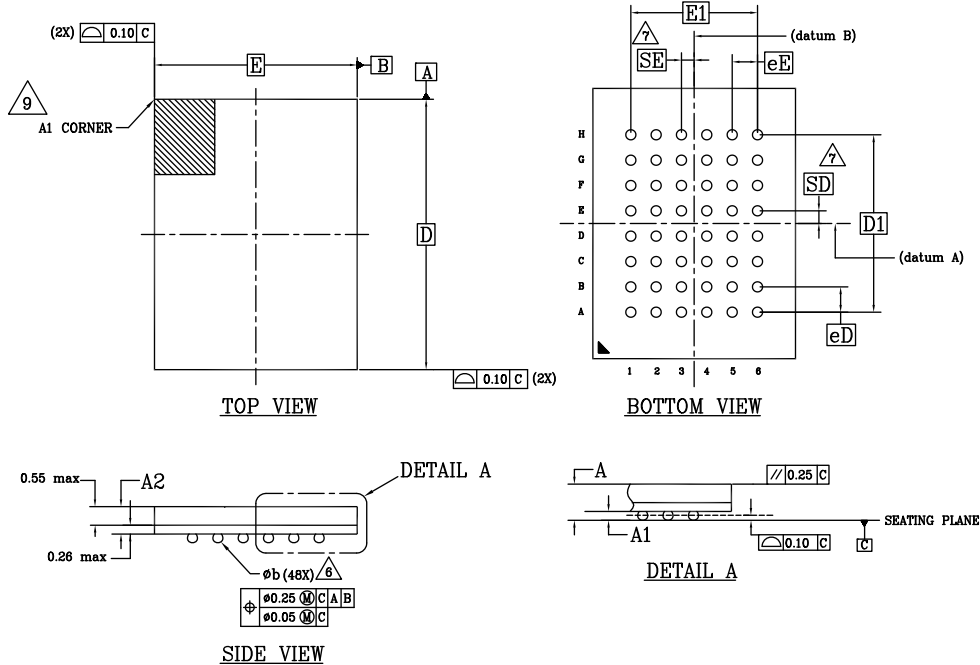
Figure 11. 44-pin TSOP II Package Outline, 51-85087



51-85087 *F

Package Diagrams (continued)

Figure 12. 48-ball VFBGA (6 × 8 × 1.0 mm) Package Outline, 51-85150



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	-	-	1,00
A1	0,16	-	-
A2	-	-	0,81
D	8,00 BSC		
E	6,00 BSC		
D1	5,25 BSC		
E1	3,75 BSC		
MD	8		
ME	6		
n	48		
∅ b	0,25	0,30	0,35
eE	0,75 BSC		
eD	0,75 BSC		
SD	0,375 BSC		
SE	0,375 BSC		

- NOTES:**
- DIMENSIONING AND TOLERANCING METHODS PER ASME Y14.5M-2009.
 - ALL DIMENSIONS ARE IN MILLIMETERS.
 - BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
 - [e] REPRESENTS THE SOLDER BALL GRID PITCH.
 - SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION, SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION, n IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
 - ∅ b DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
 - *SD* AND *SE* ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW *SD* OR *SE* = 0. WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, *SD* = eD/2 AND *SE* = eE/2.
 - ** INDICATES THE THEORETICAL CENTER OF DEPOPULATED BALLS.
 - ∅ 9 A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.

51-85150 *I

Acronyms

Table 1. Acronyms Used in this Document

Acronym	Description
$\overline{\text{BHE}}$	byte high enable
$\overline{\text{BLE}}$	byte low enable
$\overline{\text{CE}}$	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
$\overline{\text{OE}}$	output enable
SRAM	static random access memory
TTL	Transistor-transistor logic
VFBGA	very fine-pitch ball grid array
$\overline{\text{WE}}$	write enable

Document Conventions

Units of Measure

Table 2. Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microamperes
μs	microseconds
mA	milliamperes
mm	millimeters
ns	nanoseconds
Ω	ohms
%	percent
pF	picofarads
V	volts
W	watts

Document History Page

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Rev.	ECN No.	Submission Date	Description of Change
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